



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	[METHOD FOR FABRICATING A MOSFET AND REDUCING LINE WIDTH OF GATE STRUCTURE]		
Application Type : regular, utility Attorney Docket Number : 11760-US-PA			
Correspondence address: Customer Number: 31561 			
Inventor Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: TW Name prefix: Mr. Given Name: ERH-KUN Family Name: LAI Residence: City of Residence: TAICHUNG Country of Residence: TW Address-1 of Mailing Address: NO. 14, LANE 411, YOUYUAN N RD., LUNGJING SHIANG Address-2 of Mailing Address: City of Mailing Address: TAICHUNG State of Mailing Address: Postal Code of Mailing Address: Country of Mailing Address: TW Phone: Fax: E-mail:			
Attorney Information: practitioner(s) at Customer Number: 31561  as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			